



Atty. Dkt. No.	M#	Client Ref.
	309173	P-1583.010-US

**INFORMATION DISCLOSURE STATEMENT  
BY APPLICANT**

Applicant:	DE SMIT et al.
Appln. No.:	Unknown <u>10/820,217</u>
Filing Date:	April 8, 2004
Examiner:	Unknown
Group Art Unit:	Unknown

Date: May 14, 2004 Page 2 of 3

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Examiner's Initials*	Document Number	Date MM/YYYY	Name (Family Name of First Inventor)	Class	Sub Class	Filing Date (if appropriate)
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	CR 6,633,365	10/2003	SUENAGA	355	53	
	DR 2002/0163629	11/2002	SWITKES et al.	355	53	
	ER 2003/0123040	07/2003	ALMOGY	355	69	
	FR 2003/0174408	09/2003	ROSTALSKI et al.	359	642	
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					Enclosed	No	Enclose	No
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	KR JP 07-220990	08/1995	JAPAN	FUKUDA et al.	X			
	LR JP 10-228661	08/1998	JAPAN	KUROKAWA	X			
	MR JP 10-255319	09/1998	JAPAN	SUENAGA et al.	X			
	NR JP 10-303114	11/1998	JAPAN	SUWA	X		X	
	OR JP 10-340846	12/1998	JAPAN	KUDO	X		X	
	PR JP 2001-091849	04/2001	JAPAN	AIZAKI et al.	X			
	QR JP 07-132262	05/1995	Japan	HIRAKAWA et al.	X			
	RR JP 58-202448	11/1983	Japan	KAWAMURA et al.	X			
	SR WO2004/019128	03/2004	PCT	OMURA et al.				
	TR WO 03/077037	09/2003	PCT	ROSTALSKI				
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	XR	B.J. LIN, "The Paths To Subhalf-Micrometer Optical Lithography", SPIE Vol. 922, Optical/Laser Microlithography (1988), pp. 256-269			
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	ZR	S. OWA et al., "Immersion Lithography; its potential performance and issues", SPIE Microlithography 2003, 5040-186, February 27, 2003			
AM	AAR	S. OWA et al., "Advantage and Feasibility of Immersion Lithography", Proc. SPIE 5040 (2003)			

Examiner Alan Mathews

Date Considered: 2-18-2006

\*EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP § 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to Applicant.



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U.S. PATENT DOCUMENTS

Examiner's Initials*	Document Number	Date MM/YYYY	Name (Family Name of First Inventor)	Class	Sub Class	Filing Date (if appropriate)
AR						
BR						

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AM	DR DD 221 563	04/1985	GERMANY	PFORR et al.		X
ER						

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	GR	H. KAWATA et al., "Optical Projection Lithography using Lenses with Numerical Apertures Greater than Unity",	Microelectronic Engineering	9 (1989), pp. 31-36					
	HR	J.A. HOFFNAGLE et al., "Liquid Immersion Deep-Ultraviolet Interferometric Lithography",	J. Vac. Sci. Technol. B., Vol. 17, No. 6, November/December 1999,	pp. 3306-3309					
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	JR	H. KAWATA et al., "Fabrication of 0.2µm Fine Patterns Using Optical Projection Lithography with an Oil Immersion Lens",	Jpn. J. Appl. Phys. Vol. 31 (1992), pp. 4174-4177						
	KR	G. OWEN et al., "1/8µm Optical Lithography",	J. Vac. Sci. Technol. B., Vol. 10, No. 6, November/December 1992,	pp. 3032-3036					
	LR	H. HOGAN, "New Semiconductor Lithography Makes a Splash",	PHOTONICS SPECTRA, Photonics TechnologyWorld, October 2003 Edition,	pgs. 1-3					
	MR	S. OWA and N. NAGASAKA, "Potential Performance and Feasibility of Immersion Lithography",	NGL Workshop 2003, July 10, 2003, Slide Nos. 1-33.						
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	OR	H. HATA, "The Development of Immersion Exposure Tools",	Litho Forum, International SEMATECH, Los Angeles, January 27-29, 2004, Slide Nos. 1-22						
	PR	T. MATSUYAMA et al., "Nikon Projection Lens Update",	SPIE Microlithography 2004, 5377-65, March, 2004						
	QR	"Depth-of-Focus Enhancement Using High Refractive Index Layer on the Imaging Layer",	IBM Technical Disclosure Bulletin, Vol. 27, No. 11, April 1985, p. 6521						
✓	RR	A. SUZUKI, "Lithography Advances on Multiple Fronts",	EEdesign, EE Times, January 5, 2004						
AM	SR	B. LIN, "The $k_3$ coefficient in nonparaxial MNA scaling equations for resolution, depth of focus, and Immersion lithography",	J. Microlith, Microfab, Microsyst. 1(1):7-12 (2002)						
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	CR 4,346,184	08/1982	TABARELLI et al.	430	311	
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	OR EP 0418427	03/1991	EUROPE	MIYAKE	X		X	
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	RR DD 242880	02/1987	GERMANY	KUCH		X		
	SR FR 2474708	07/1981	FRANCE	LETELLIER		X		
	TR JP 62-085326	03/1987	JAPAN	MORIUCHI	X			
	UR JP 62-121417	06/1987	JAPAN	NAKAZAWA	X			
	VR JP 63-157419	08/1988	JAPAN	NAKASUJI	X			
	WR JP 04-305915	10/1992	JAPAN	OZEKI et al.	X			
AM	XR JP 04-305917	10/1992	JAPAN	OZEKI et al.	X			

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AM -	YR	EP Search Report for EP 03253694.8 dated March 30, 2004					
	ZR	M. SWITKES et al., "Immersion Lithography at 157 nm", MIT Lincoln Lab, Orlando 2001-1, December 17, 2001					
	AAR	M. SWITKES et al., "Immersion Lithography at 157 nm", J. Vac. Sci. Technol. B., Vol. 19, No. 6, November/December 2001, pp. 2353-2356					
AM -	BBR	M. SWITKES et al., "Immersion Lithography: Optics for the 50 nm Node", 157 Anvers-1, September 4, 2002					

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